MOSFETs Silicon N-Channel MOS (U-MOSVI-H)

TPC8228-H

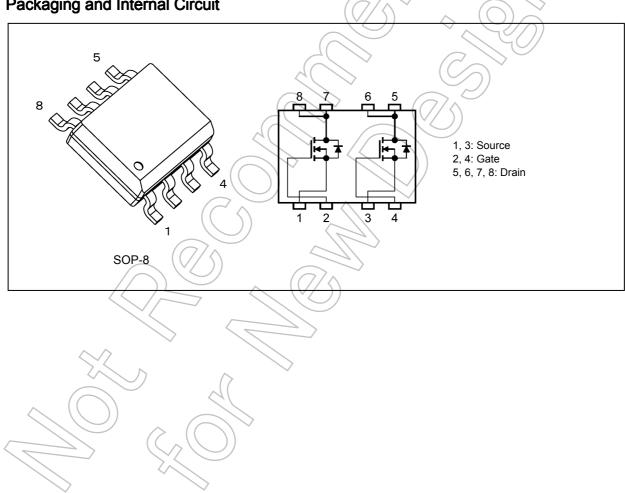
1. Applications

- DC-DC Converters •
- **CCFL** Inverters

2. Features

- (1) Small, thin package
- (2) High-speed switching
- (3)Small gate charge: Q_{SW} = 2.6 nC (typ.)
- (4) Low drain-source on-resistance: $R_{DS(ON)} = 38 \text{ m}\Omega$ (typ.)
- (5) Low leakage current: $I_{DSS} = 10 \ \mu A \ (max) \ (V_{DS} = 60 \ V)$
- (6) Enhancement mode: $V_{th} = 1.3$ to 2.3 V ($V_{DS} = 10$ V, $I_D = 0.1$ mA)

3. Packaging and Internal Circuit



4. Absolute Maximum Ratings (Note) (Ta = 25°C unless otherwise specified)

Characteristics			Symbol	Rating	Unit
Drain-source voltage			V _{DSS}	60	V
Gate-source voltage			V _{GSS}	±20	
Drain current (DC)		(Note 1)	ID <	3.8	A
Drain current (pulsed)		(Note 1)	I _{DP}	15.2	
Power dissipation (single operation)	(t = 10 s)	(Note 2), (Note 4)	P _{D(1)}	1.5	W
Power dissipation (per device for dual operation)	(t = 10 s)	(Note 2), (Note 5)	P _{D(2)}	1.1	
Power dissipation (single operation)	(t = 10 s)	(Note 3), (Note 4)	P _{D(1)}	0.75	
Power dissipation (per device for dual operation)	(t = 10 s)	(Note 3), (Note 5)	P _{D(2)}	0.45	
Single-pulse avalanche energy		(Note 6)	EAS	10	mJ
Avalanche current			J _{AR}	3.8	A
Channel temperature		$\langle \langle$	T _{ch}	150	°C
Storage temperature			◯ T _{stg}	-55 to 150	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

5. Thermal Characteristics

Characteristics		Symbol	Max	Unit
Channel-to-ambient thermal resistance (single operation)	(t = 10 s) (Note 2), (Note 4)	R _{th(ch-a)(1)}	83.3	°C/W
Channel-to-ambient thermal resistance (per device for dual operation)	(t = 10 s) (Note 2), (Note 5)	R _{th(ch-a)(2)}	113	
Channel-to-ambient thermal resistance (single operation)	(t = 10 s) (Note 3), (Note 4)	R _{th(ch-a)(1)}	166	
Channel-to-ambient thermal resistance (per device for dual operation)	(t = 10 s) (Note 3), (Note 5)	R _{th(ch-a)(2)}	277	

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: Device mounted on a glass-epoxy board (a), Figure 5.1

Note 3: Device mounted on a glass-epoxy board (b), Figure 5.2

Note 4: Power dissipation and thermal resistance values per device with the other device being off (During single operation, power is supplied to only one of the two devices.)

Note 5: Power dissipation and thermal resistance values per device for dual operation (During dual operation, power is evenly supplied to both devices.)

Note 6: V_{DD} = 24 V, T_{ch} = 25°C (initial), L = 1.0 mH, I_{AR} = 3.8 A

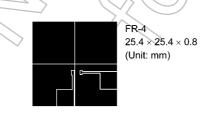
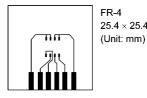
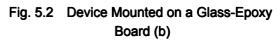


Fig. 5.1 Device Mounted on a Glass-Epoxy

Board (a)



 $25.4 \times 25.4 \times 0.8$



Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

6. Electrical Characteristics

6.1. Static Characteristics (Ta = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I _{GSS}	V_{GS} = ±20 V, V_{DS} = 0 V	_	—	±0.1	μA
Drain cut-off current	I _{DSS}	V _{DS} = 60 V, V _{GS} = 0 V	Y	_	10	
Drain-source breakdown voltage	V _{(BR)DSS}	I _D = 10 mA, V _{GS} = 0 V	60		—	V
Drain-source breakdown voltage (Note 7)	V _{(BR)DSX}	I _D = 10 mA, V _{GS} = -20 V	43)7	_	
Gate threshold voltage	V _{th}	V _{DS} = 10 V, I _D = 0.1 mA	1.3	2_	2.3	
Drain-source on-resistance	R _{DS(ON)}	V_{GS} = 4.5 V, I _D = 1.9 A	7	43	64	mΩ
		V _{GS} = 10 V, I _D = 1.9 A	\sum	38	57	

Note 7: If a reverse bias is applied between gate and source, this device enters V_{(BR)DSX} mode. Note that the drainsource breakdown voltage is lowered in this mode.

6.2. Dynamic Characteristics ($T_a = 25^{\circ}C$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C _{iss}	V_{DS} = 10 V, V_{GS} = 0 V, f = 1 MHz)(640) —	pF
Reverse transfer capacitance	C _{rss}		\mathcal{A}	25		
Output capacitance	C _{oss}		\sim	> 90	_	
Gate resistance	r _g	V _{DS} = 10 V, V _{GS} = 0 V, f = 5 MHz	()	3.2	4.6	Ω
Switching time (rise time)	tr	See Figure 6.2.1.	\sim	1.8	—	ns
Switching time (turn-on time)	t _{on}))—	6.7	_	
Switching time (fall time)	t _f		_	1.8	—	
Switching time (turn-off time)	t _{off}		—	18	_	

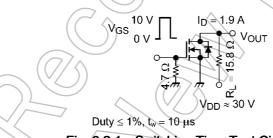


Fig. 6.2.1 Switching Time Test Circuit

6.3. Gate Charge Characteristics ($T_a = 25^{\circ}C$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus	Qg	$V_{DD} \approx 48 \text{ V}, \text{ V}_{GS} \text{ = } 10 \text{ V}, \text{ I}_{D} \text{ = } 3.8 \text{ A}$	_	11	_	nC
gate-drain)		$V_{DD} \approx 48$ V, V_{GS} = 5 V, I_D = 3.8 A		5.7	_	
Gate-source charge 1	Q _{gs1}	$V_{DD} \approx 48$ V, V_{GS} = 10 V, I_D = 3.8 A	_	2.1	—	
Gate-drain charge	Q _{gd}		_	1.8	_	
Gate switch charge	Q _{SW}			2.6	_	

6.4. Source-Drain Characteristics ($T_a = 25^{\circ}C$ unless otherwise specified)

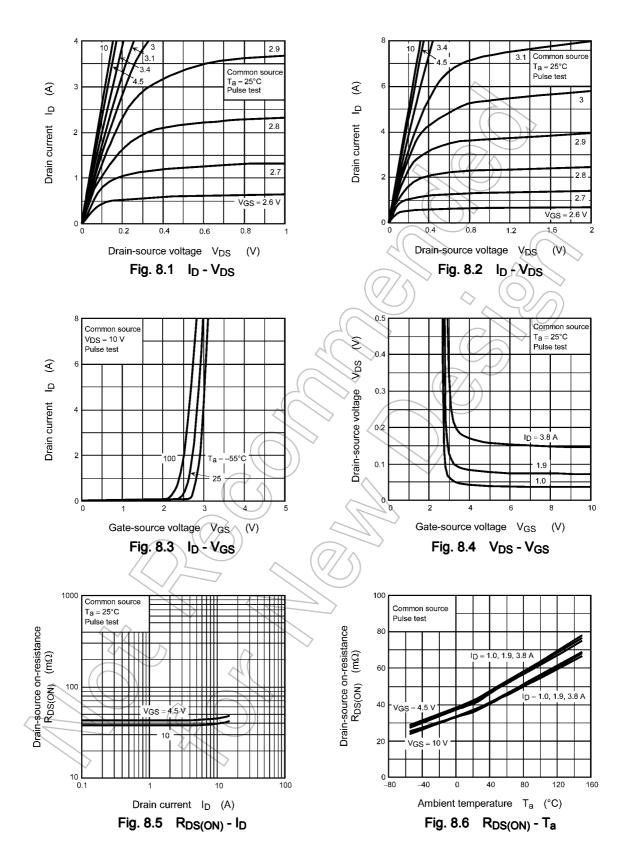
Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Reverse drain current (pulsed)	(Note 8)	I _{DRP}	—	_	_	15.2	А
Diode forward voltage		V_{DSF}	I _{DR} = 3.8 A, V _{GS} = 0 V			-1.2	V

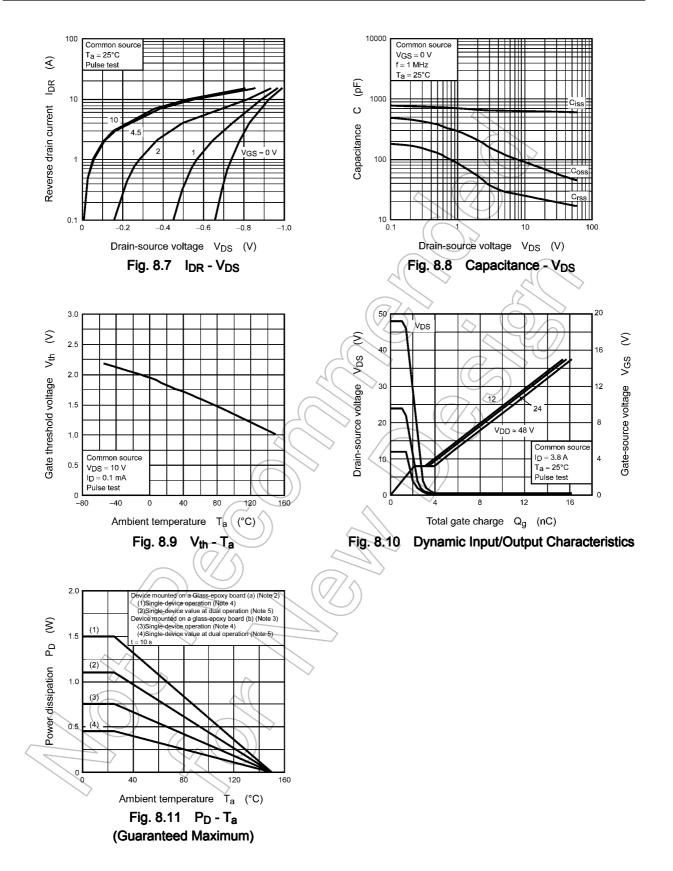
Note 8: Ensure that the channel temperature does not exceed 150°C.

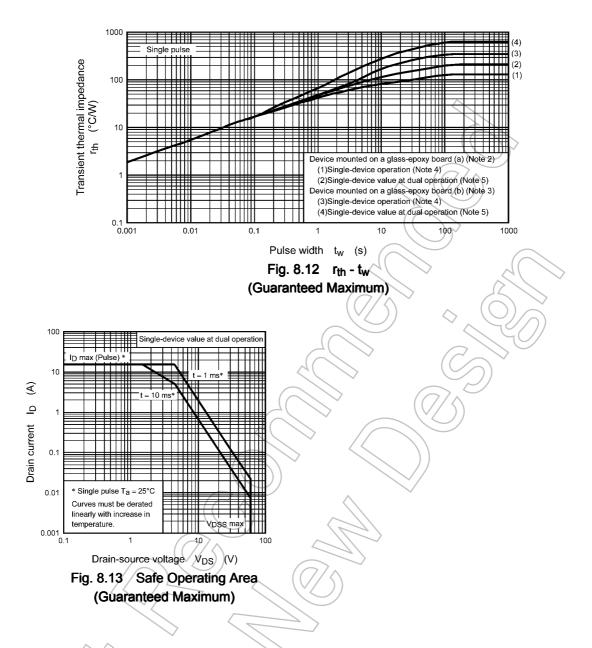
TOSHIBA 7. Marking (Note)

	Pin #1 Fig. 7.1 Marking
Note:	A line under a Lot No. identifies the indication of product Labels. Not underlined: [[Pb]]/INCLUDES > MCV Underlined: [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]] Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product.
	The RoHS is the Directive 2011/65/EU of the European Parliament and of the Council of 8 June 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.

8. Characteristics Curves (Note)







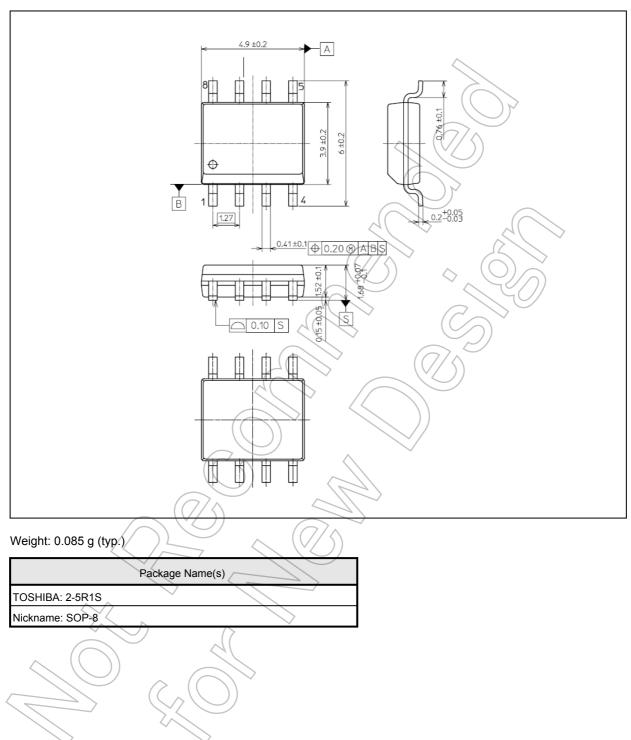
Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



TPC8228-H

Package Dimensions

Unit: mm



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